Study of structural and optoelectronic properties of Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)Se$_4$ ($x$ = 0 to 1) alloy compounds

M. Grossberg *, K. Timmo, T. Raadik, E. Kärber, V. Mikli, J. Krustok

Department of Materials Science, Tallinn University of Technology, Ehitajate tee 5, 19086 Tallinn, Estonia

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In this work, the optoelectronic and structural properties of Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)Se$_4$ (CZTGeSe) alloy compounds with $x$ varying from 0 to 1 with a step of 0.1 were studied. The crystal structure and the lattice parameters of the CZTGeSe polycrystals were determined by using X-ray diffraction analysis. A linear decrease of the lattice parameter $a$ from 0.569 nm to 0.561 nm with increasing Ge concentration was detected. Raman spectroscopy analysis revealed unimodal behavior and a linear shift of the three A symmetry Raman modes of kesterite crystal structure towards higher wavenumbers with increasing Ge content. Radiative recombination processes in CZTGeSe polycrystals were studied by using low-temperature photoluminescence (PL) spectroscopy. A continuous shift from 0.955 eV to 1.364 eV of the PL band position with increasing Ge concentration was detected. Based on the temperature dependent PL measurements of the CZTGeSe polycrystals, two types of recombination mechanisms were detected: band to impurity recombination in Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)Se$_4$ with $x$ ≤ 0.2, and band to tail recombination in Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)Se$_4$ with $x$ > 0.2.

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1. Introduction

The I$_2$–II–IV–VI$_4$ (I = Cu, Ag; II = Zn, Cd; IV = Si, Ge, Sn; VI = S, Se) series of quaternary chalcogenide semiconductors have drawn wide interest for their application as solar cell absorbers. Cu$_2$ZnSn$_{1-x}$Se$_4$ (CZTSe) based solar cells have recently achieved solar energy conversion efficiency of 12.6% [1]. The bandgap energy of CZTSe solid solutions can be tailored by varying the S/Se ratio to reach the optimum for solar energy conversion value of around 1.4 eV. In this study we show additional ability for tuning bandgap of CZTSe through substitution of Sn by Ge atoms in the cation sublattice, it is difficult to distinguish between the kesterite and stannite structure by conventional X-ray diffraction (XRD). By using neutron scattering analysis that can differentiate between the kesterite and stannite structure, Schorr et al. [15] have reported CZTSe to crystallize in the kesterite structure. It was recently shown by Guc et al. [16] by using polarization dependent Raman scattering analysis that CZGeSe and CZTSe show vibrational spectra characteristic of the kesterite crystal structure. The radiative recombination mechanisms in the kesterites like CTS and CZTSe are still under debate and there are only few reports about the PL of CZTSe, CZGeSe and their solid solutions. In low-temperature PL measurements, broad asymmetric PL band at around 0.95 eV resulting from band-to-impurity (BI) recombination is usually detected in CZTSe [17–20], also excitonic emission at 1.033 eV together with donor–acceptor pair recombination at 0.989 eV involving shallow defects has been reported [12]. Bag et al. [2] have presented a broad PL spectrum

* Corresponding author.

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of Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)$_4$ with $x = 0.4$ at 1.05 eV. Timmo et al. [9] have reported a broad asymmetric PL spectrum of CZGeSe at 1.26 eV. The results of the present study show the structural and vibrational properties together with the dominating recombination mechanisms of Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)$_4$ polycrystals with $x$ varying from 0 to 1 with a step of 0.1.

2. Experimental

Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)$_4$ polycrystalline powders were synthesized from Cu, Zn, Sn, and Ge elemental metal powders and elemental Se in evacuated quartz ampoules. All precursors were grounded in an agate mortar in intended quantities and ratios. After mixing and grounding the precursors, the mixture was poured into a quartz ampoule, degassed under dynamic vacuum, sealed, and annealed isothermally at 1013 K for 168 h and at 823 K for 168 h. After annealing at 823 K, ampoules were cooled down with furnace to room temperature. In addition, post-growth heat treatment at 1013 K for 35 min was performed. After annealing the ampoules were cooled down with furnace to room temperature. The chemical composition of the Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)$_4$ polycrystals was determined by energy dispersive spectroscopy (EDS) on scanning electron microscope Zeiss ULTRA 55 operating at accelerating voltage 20 kV and using Röntec EDX XFlash 3001 detector. Powder XRD patterns were recorded on a Rigaku Ultima IV diffractometer with Cu K$_\alpha$ radiation ($\lambda = 1.5406$ Å). Rietveld method was used for the derivation of crystal structure information from powder XRD data. The micro-Raman spectra were recorded by using a Horiba’s LabRam HR800 spectrometer and 532 nm laser line that was focused on the sample with spot size of about 5 μm. For PL measurements, the samples were mounted in the closed-cycle He cryostat. The 405 nm laser line was used for PL excitation and InGaAs detector for signal detection.

3. XRD results

According to EDS analysis a linear substitution of Sn with Ge is observed in the CZTGeSe polycrystalline powders with initial composition of Cu$_{1.82}$Zn$_{1.18}$Sn$_{1-x}$Ge$_x$Se$_{4.02}$ with $x$ from 0 to 1 with a step of 0.1, as presented in Fig. 1. Only for the CZTGeSe powder with $x = 0.2$ a deviation from the linear trend in composition was detected. The synthesized powders showed increase in the Cu content with increasing Ge content, probably due to the narrower single phase formation region of CZGeSe. XRD patterns of Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)$_4$ polycrystals in dependence of the $x$ value were recorded. Lattice shrinkage with increasing substitution for the smaller Ge ion results in a systematic shift in the diffraction peaks to higher angles. From the diffraction patterns the lattice parameters were determined by using Rietveld refinements. The obtained values for CZTGeSe are in agreement with the data reported by Morihama et al. [3]. A linear trend in lattice parameters was observed (see Fig. 2a) indicating a homogenous element distribution within each powder and the substitution of tin by germanium in Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)$_4$. The tetragonal distortion parameter $\eta = c / 2a$ in dependence of the Ge content in the Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)$_4$ powders is shown in Fig. 2b. For all the studied powders $\eta < 1$ that according to the theoretical predictions [21,22] is characteristic of the kesterite structure. Our findings are in very good agreement with the results reported by Morihama et al. [3].

4. Raman analysis results

The Raman spectra of Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)$_4$ polycrystals are presented in Fig. 3. The Raman peaks of CZTSe are in agreement with previous reports [16,17,23,24] and can be detected at 81, 157, 173, 196, 223, 234, and 245 cm$^{-1}$. The Raman peak positions of CZGeSe are also in agreement with previous reports by Timmo et al. [9] and Guc et al. [16] and were detected at 92, 174, 178, 205, 271, 283 and 292 cm$^{-1}$. Guc et al. [16] have performed detailed polarization dependent Raman analysis on CZGeSe and CZTSe crystals and assigned the detected Raman peaks to the corresponding symmetry modes characteristic of the kesterite type crystal structure. The irreducible representation for the zone center phonon modes for kesterite type structure with space group $I$4 is [24]:

$$\Gamma = 3A + 6B + 6E,$$

where all modes are Raman active. The three A modes characteristic for the kesterite structure can be detected at 168, 173, and 196 cm$^{-1}$ in the Raman spectrum of CZTSe polycrystalline powder and at 174, 178, and 205 cm$^{-1}$ in the Raman spectrum of CZGeSe powder. Frequencies of all A modes corresponding to the vibrations of anion atoms shift linearly with $x$ in Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)$_4$ between the positions for CZTSe and CZTGeSe showing the expected unimodal behavior characteristic of alloy compounds where cations are substituted. Also, there was no
significant broadening of the A modes with cation substitution. Accordingly, Raman results suggest kesterite crystal structure for the whole solid solution series of Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)Se$_4$ polycrystals.

5. Photoluminescence results

Low-temperature (T = 10 K) PL spectra of Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)Se$_4$ polycrystals in dependence of the x value are presented in Fig. 4. A continuous shift from 0.955 eV to 1.364 eV of broad and asymmetric PL band with increasing value of x from 0 to 1, is detected. The asymmetric shape of the PL band is characteristic to the semiconductor material with spatial potential fluctuations that are commonly present in the compensated multinary compounds with high native defect concentrations [17,25,26]. The PL spectra of studied Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)Se$_4$ polycrystals show large blueshift in the order of about 15 meV/decade with increasing laser power that is also characteristic to a material with spatial potential fluctuations [25,26]. The PL band of CZTSe at 0.95 eV shows the same behavior and thermal activation energy of 70 meV as was also observed in our previous study [17]. Accordingly, it can be attributed to BI recombination involving an acceptor defect with ionization energy of 70 meV. The PL band shifts towards higher energies with increasing Ge concentration almost following the bandgap energy dependence on Ge content presented by Morihama et al. [3] indicating change in the recombination mechanism. Note that room temperature bandgap energy values with 0.2 increments in x were given in [3]. Solid lines present polynomial fits of the dependencies.

![Fig. 4. Low-temperature PL spectra of Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)Se$_4$ polycrystals with varying values of x. The PL peaks relate to 0.1 increments in x from left to right. The inset graph shows shift of the detected PL band peak position (solid dots) that is slightly steeper than the bandgap energy dependence (hollow dots) on Ge content as presented by Morihama et al. [3] indicating change in the recombination mechanism. Note that room temperature bandgap energy values with 0.2 increments in x were given in [3]. Solid lines present polynomial fits of the dependencies.](image1)

![Fig. 5. Raman spectra of Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)Se$_4$ polycrystals in dependence of the x value. The inset graph shows the linear shift of the peak positions of the three A symmetry modes towards higher wavenumbers with increasing Ge content.](image2)

![Fig. 3. Raman spectra of Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)Se$_4$ polycrystals in dependence of the x value. The inset graph shows the linear shift of the peak positions of the three A symmetry modes towards higher wavenumbers with increasing Ge content.](image3)

![Fig. 5. Thermal activation energies $E_T$ (solid dots) obtained from the temperature dependences of the PL spectra of Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)Se$_4$ polycrystals. The average depth of the spatial potential fluctuations $\gamma$ in Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)Se$_4$ is presented with hollow dots.](image4)

In $\ln(T)$ versus 1000/T at high temperatures was fitted by using theoretical expression for discrete energy levels [27]:

$$\phi_l(T) = \frac{\phi_0}{1 + \alpha_1 T^{3/2} + \alpha_2 T^{3/2} \exp \left(-\frac{E_l}{kT}\right)},$$

where $\phi_l$ is integrated intensity, $\alpha_1$ and $\alpha_2$ are the process rate parameters and $E_l$ is the thermal activation energy. The obtained thermal activation energies $E_l$ (see Fig. 5) for Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)Se$_4$ polycrystals with $x \leq 0.2$ are in the range from 43 to 70 meV. Thermal activation energies in the range from 11 to 27 meV were obtained for Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)Se$_4$ powders with $x > 0.2$. It was also observed that for Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)Se$_4$ with $x > 0.2$, the PL band becomes more asymmetric with more pronounced exponential low-energy side that is characteristic for BT recombination. BT band results from recombination of free electrons and holes localized in the valence band tail caused by the spatial potential fluctuations. The potential fluctuations lead to local perturbation of the band structure, thus broadening the defect level distribution and forming band tails. The density of the band tail states usually has an exponential shape resulting in an exponential tail of the low-energy side of the PL band. The BI recombination involves deeper acceptor defects that do not overlap with the valence band tail. The average depth of the spatial potential fluctuations $\gamma$ can be determined from the shape of the low-energy side of the PL band (see details in Refs. [25,26]) and was found to vary in between 17 and 32 meV in studied CZTGeSe (see Fig. 5). Accordingly, one could conclude that in the studied CZTGeSe polycrystals with $x \leq 0.2$ BI recombination dominates since the depth of the fluctuations is smaller than the obtained thermal activation energies resembling the ionization energies of the corresponding acceptor defects. In CZTGeSe polycrystals with $x > 0.2$, the BT recombination dominates. In case of BT recombination, the obtained thermal activation energies enable us to estimate the ionization energy of the pseudo-acceptor defects in the valence band tail that is in the range from 11 to 27 meV. The observed change in the recombination mechanism can also be seen in the steeper dependence of the PL band peak position on the Ge content in comparison to the bandgap energy (see inset graph in Fig. 4).

6. Conclusion

Cu$_2$Zn(Sn$_{1-x}$Ge$_x$)Se$_4$ polycrystalline powders with x varying from 0 to 1 were studied by XRD, Raman scattering and PL spectroscopy. The kesterite crystal structure of CZTGeSe was determined from the XRD and Raman analyses. Based on the temperature dependent PL measurements of the CZTGeSe polycrystals, two types of recombination mechanisms were detected: BI recombination in
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